

/ Descriptions

TO-252 PNP Silicon PNP transistor in a TO-252 Plastic Package.

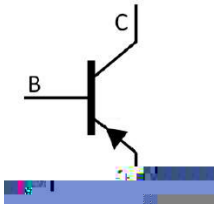
/ Features

MJD41C
Complement to MJD41C.

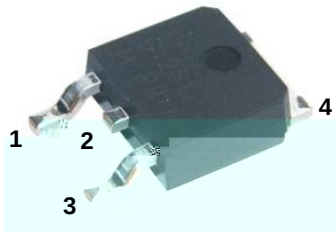
/ Applications

Medium power linear switching applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2,4 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

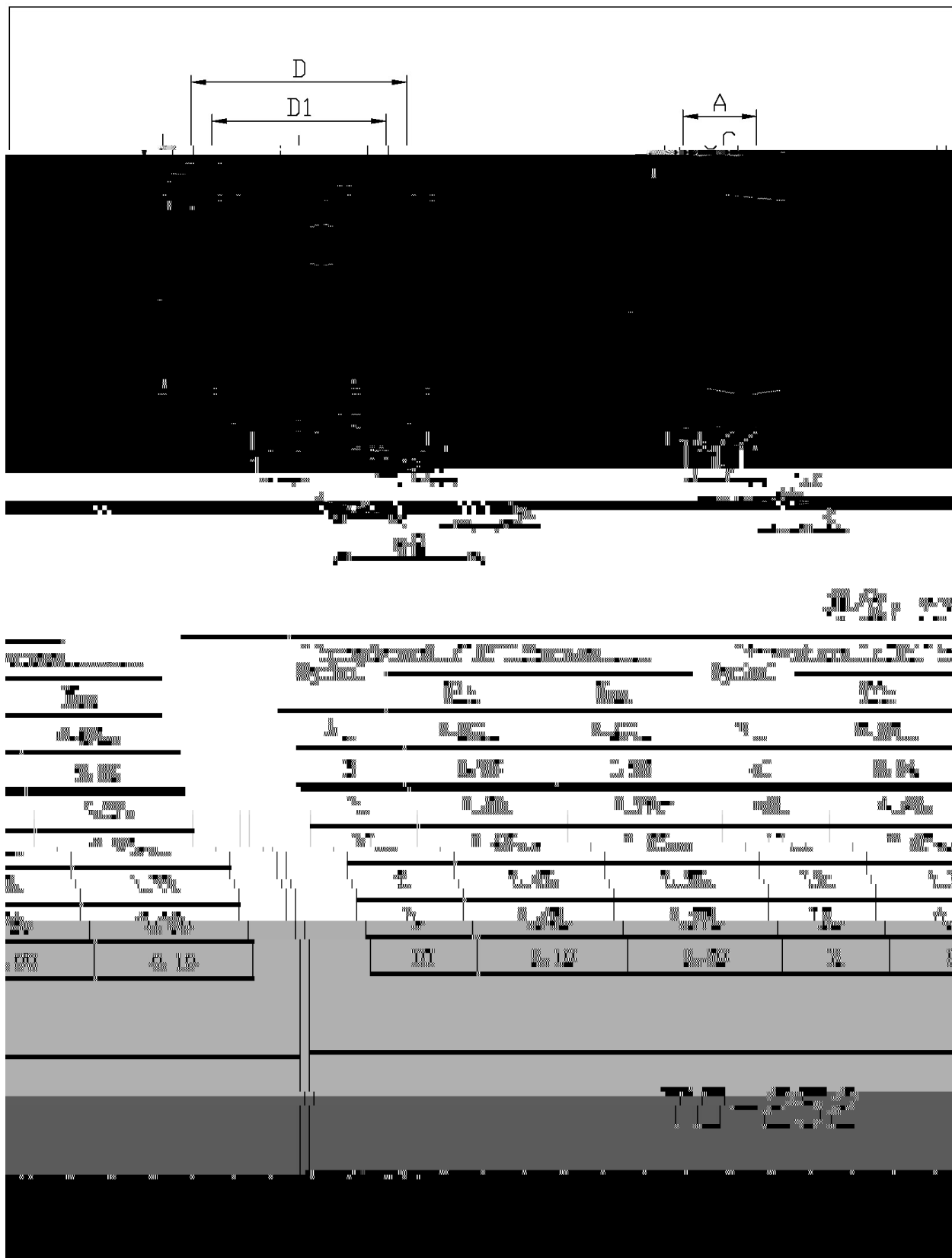
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-6.0	A
Base Current - Continuous	I_B	-2.0	A
Collector Power Dissipation	P_D	1.75	W
Collector Power Dissipation	$P_D(T_C=25^\circ C)$	20	W
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

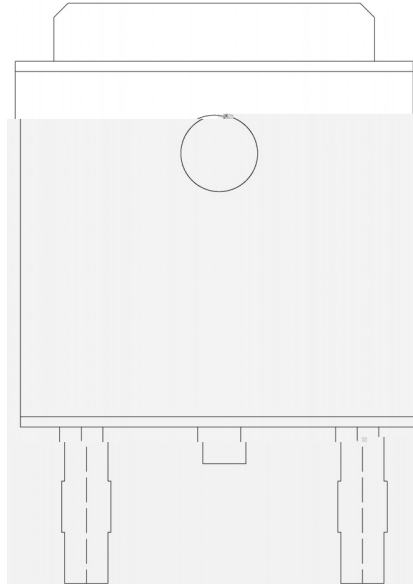
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-30mA$ $I_B=0$	-100			V
Collector Cut-Off Current	I_{CEO}	$V_{CE}=-60V$ $I_B=0$			-50	A
Collector Cut-Off Current	I_{CES}	$V_{CE}=-100V$ $V_{BE}=0$			-10	A
Emitter Cut-Off Current	I_E					

/ Electrical Characteristic Curve

/ Package Dimensions



/ Marking Instructions



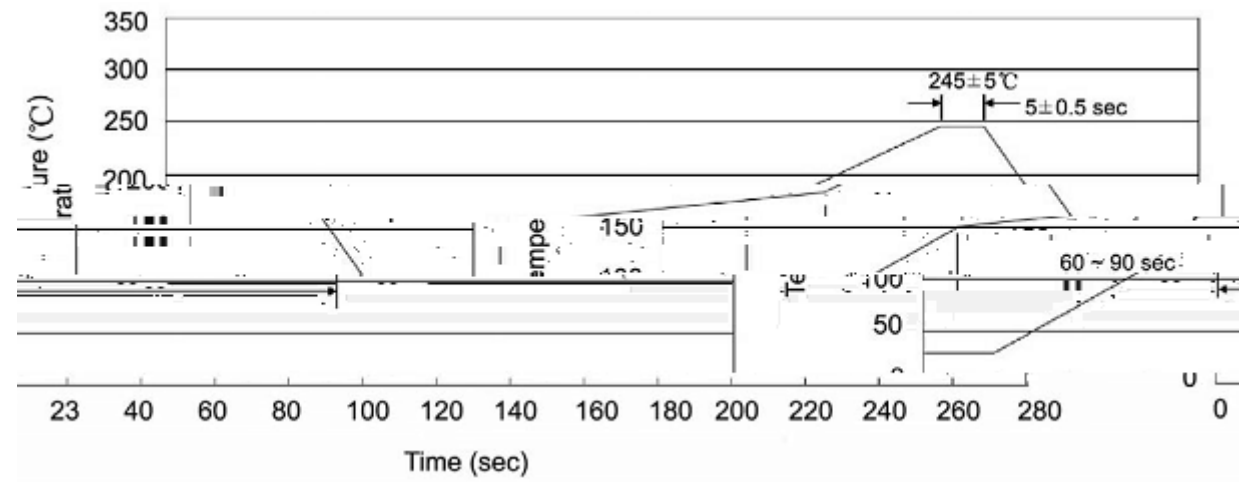
BR

MJD42C

Note:

BR:

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|----|-----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245±5 | | | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units	Dimension	(unit mm ³)
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